



semi

C3 Semiconductor, LLC

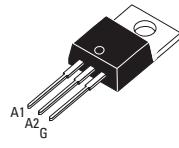
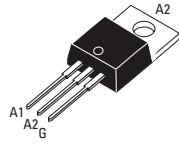
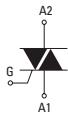
**Applications**

- Phase Control
- Static Switching
- Light Dimming
- Motor Speed Control
- Kitchen Equipment
- Power Tools
- Solenoid Valve Controls:
  - Dishwashers
  - Washing Machines

- > Suitable for General Purpose AC Switching
- > Alternistor/No Snubber Versions for Inductive Loads
- > Logic Level Available for use with Microcontrollers and Low Level Devices
- > IGT Range 35-50 mA (Q1)
- > V<sub>DRM</sub>/V<sub>RMM</sub> 400, 600, 800, 1000V

**CTA/CTB24**

25Amp - 400/600/800/1000V - TRIAC

TO-220AB Isolated  
(CTA24)TO-220AB Non-Isolated  
(CTB24)**Absolute Maximum Ratings**

	CONDITIONS	SYMBOL	RATING
RMS On-State Current (full sine wave)	T <sub>c</sub> = 100°C T <sub>c</sub> = 75°C	I <sub>TRMS</sub>	25A
Non Repetitive Surge Peak On-State Current (Full Cycle, T <sub>j</sub> Initial = 25°C)	F = 50 Hz F = 60 Hz	I <sub>TSM</sub>	250A 260A
I <sup>2</sup> t Value for fusing	t <sub>p</sub> = 10 ms	I <sup>2</sup> t	340A <sup>2</sup> s
Critical rate of rise of on-state current I <sub>G</sub> =2 x I <sub>GT</sub> , t <sub>r</sub> <100 ns, T <sub>j</sub> = 125°C	di/dt		100A/μs
Peak Gate Current @ T <sub>j</sub> = 125°C	t <sub>p</sub> = 20 μs	I <sub>GM</sub>	4A
Average Gate Power Dissipation @ T <sub>j</sub> = 125°C		P <sub>G(AV)</sub>	1W
Storage Temperature Range		T <sub>stg</sub>	-40 to +150°C
Operating Junction Temperature Range		T <sub>j</sub>	-40 to +125°C
Isolation Voltage (CTA Series only)		V <sub>ISO</sub>	2500 V <sub>RMS</sub>

**Electrical Characteristics**

## ALTERNISTOR/NO SNUBBER AND LOGIC LEVEL (3 Quadrants)

	CW	BW
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω NOTE 1	QI-II-III	35mA
V <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω	QI-II-III	1.3V
V <sub>GD</sub> MIN @ V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3kΩ	T <sub>j</sub> = 125°C	QI-II-III
I <sub>H</sub> MAX @ I <sub>T</sub> = 500 mA NOTE 2		0.2V
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>		50mA
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	Q-I	70mA
dv/dt MIN @ V <sub>D</sub> = 67%V <sub>DRM</sub> (gate open) NOTE 2	T <sub>j</sub> = 125°C	80mA
(di/dt)c MIN without Snubber NOTE 2	T <sub>j</sub> = 125°C	100mA
		13A/ms
		22A/ms

## STANDARD (4 Quadrants)

	B
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω NOTE 1	QI-II-III
I <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω NOTE 1	QIV
V <sub>GT</sub> MAX @ V <sub>D</sub> = 12 V, R <sub>L</sub> = 30Ω	Q-AII
V <sub>GD</sub> MIN @ V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3kΩ	T <sub>j</sub> = 125°C
I <sub>H</sub> MAX @ I <sub>T</sub> = 500 mA NOTE 2	Q-AII
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	QI-III-IV
I <sub>L</sub> MAX @ I <sub>G</sub> = 1.2 I <sub>GT</sub>	Q-II
dv/dt MIN @ V <sub>D</sub> = 67%V <sub>DRM</sub> (gate open) NOTE 2	T <sub>j</sub> = 125°C
(dv/dt)c MIN @ (di/dt)c = 13.3 A/ms NOTE 2	500V/μs
	10V/μs

**ISO9001 Certified****GENERAL NOTES**

1. Minimum IGT is guaranteed at 5% of IGT max.
2. For both polarities of A2 referenced to A1
3. All parameters at 25 degrees C unless otherwise specified.



semi

C3 Semiconductor, LLC

CTA/CTB24

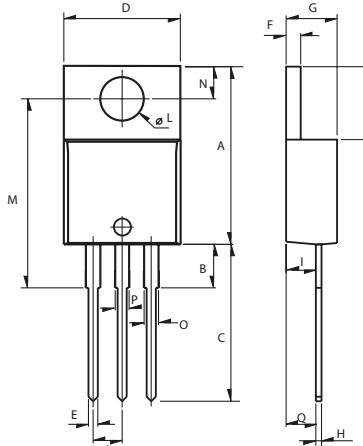
25Amp - 400/600/800/1000V - TRIAC

### Static Characteristics

$V_T$ MAX @ $I_{TM} = 35$ A, $t_p = 380\mu s$ <sup>NOTE 2</sup>	$T_j = 25^\circ C$	1.55V
$V_{to}$ MAX @ Threshold Voltage <sup>NOTE 2</sup>	$T_j = 125^\circ C$	0.85V
$R_d$ MAX @ Dynamic Resistance <sup>NOTE 2</sup>	$T_j = 125^\circ C$	16Ω
$I_{DRM}$ MAX @ $V_{DRM} = V_{RRM}$	$T_j = 25^\circ C$	5μA
$I_{RRM}$ MAX @ $V_{DRM} = V_{RRM}$	$T_j = 125^\circ C$	3mA

### Thermal Resistances

Junction to Case (AC)	TO-220AB	SYMBOL	RATING
Junction to Case (AC)	TO-220AB Isolated	R <sub>th(j-c)</sub>	0.8°C/W
Junction to Ambient	TO-220AB	R <sub>th(j-a)</sub>	60°C/W
Junction to Ambient	TO-220AB Isolated	R <sub>th(j-a)</sub>	60°C/W



### Dimensions

REF.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.24		15.75	0.6		0.62
B		3.23			0.127	
C	12.78		13.79	0.503		0.543
D	9.96		10.36	0.392		0.408
E	0.69		0.94	0.027		0.037
F	1.22		1.32	0.048		0.052
G	4.62		4.83	0.182		0.19
H	0.46		0.61	0.018		0.024
I	2.49		2.84	0.098		0.112
J	2.39		2.69	0.094		0.106
K	6.48		6.88	0.255		0.271
L	3.78		3.89	0.149		0.153
M	15.49	16	16.51	0.61	0.63	0.65
N	2.59		2.9	0.102		0.114
O	0.99		1.55	0.039		0.061
P	0.99		1.55	0.039		0.061
Q		2.67			0.105	

### Part Number Selection

Part Number	Voltage [Vpk]	$\delta t$ [mA]	Type	Package
CTA/CTB24-xxxB	400, 600, 800, 1000	50mA	Standard	TO-220AB
CTA/CTB24-xxxBW	400, 600, 800, 1000	50mA	Alternistor/No Snubber	TO-220AB
CTA/CTB24-xxxCW	400, 600, 800, 1000	35mA	Alternistor/No Snubber	TO-220AB

### Part Number Designation

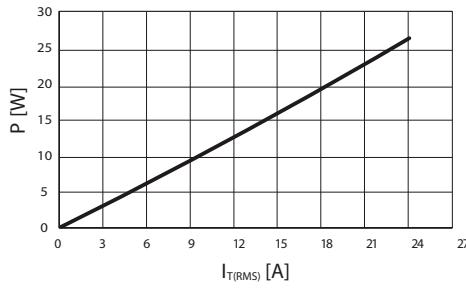
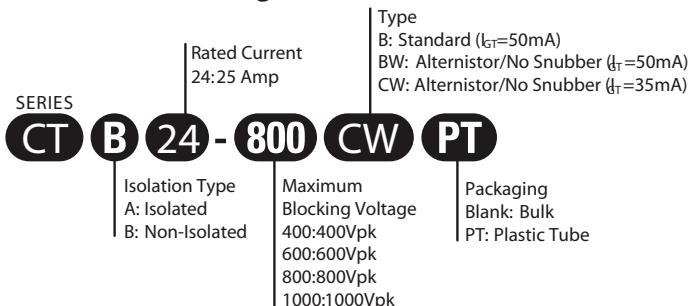


Fig. 1: Power dissipation versus RMS on-state current (full cycle).

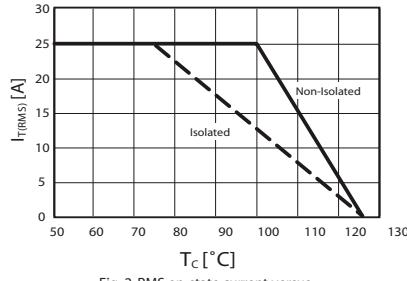


Fig. 2: RMS on-state current versus case temperature (full cycle)

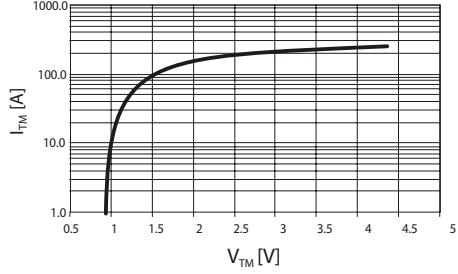


Fig. 3: On-state current versus on-state voltage (instantaneous values)

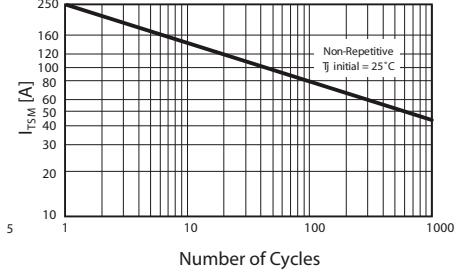


Fig. 4: Non-repetitive surge peak on-state current versus number of cycles.

ISO9001 Certified

© 2007 C3 Semiconductors, Specifications subject to change without notice.

For recommended applications and more information contact:  
USA: Sales Support (888) 882-8689

Email: sales@c3semi.com WEB SITE: http://www.C3semi.com

Approvals

UL - E72445